

FIG.1

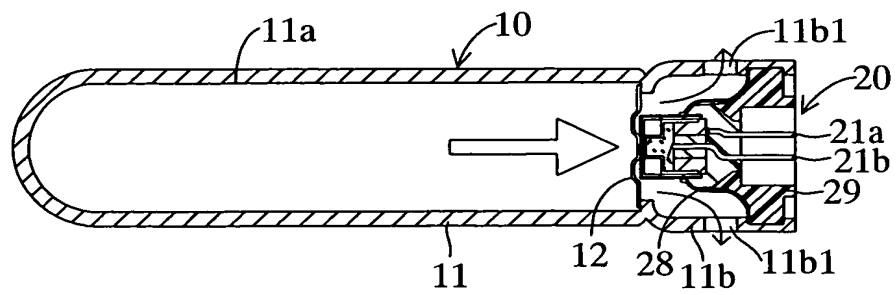


FIG.2

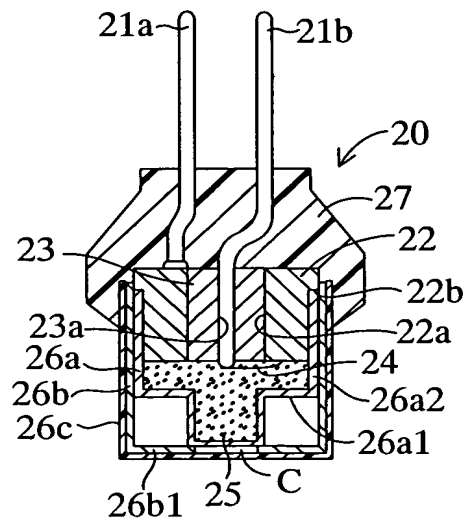


Figure 1 is a schematic diagram of a cross-section of a semiconductor device. The device has a central core 26a with a top layer 26a1. The core 26a is surrounded by a material 26a2. The thicknesses of the layers are indicated by arrows: t1 for the bottom layer, t2 for the side layer, t3 for the top layer, and t4 for the outer layer.

FIG.5

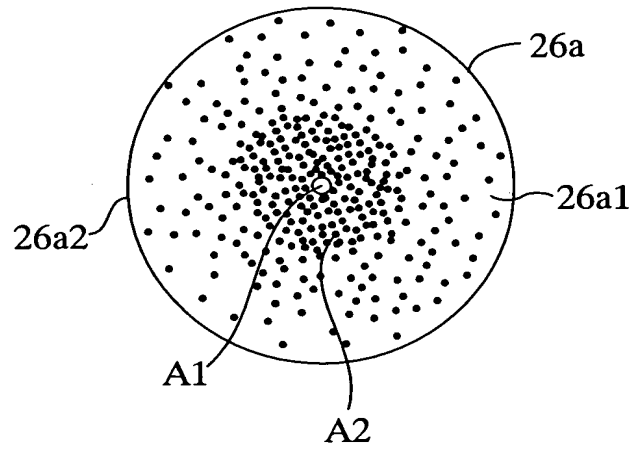


FIG.6

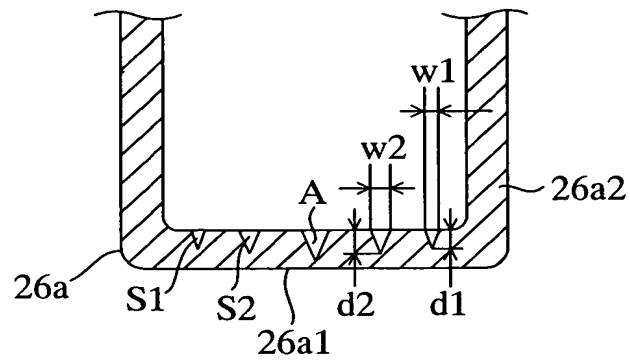


FIG. 7

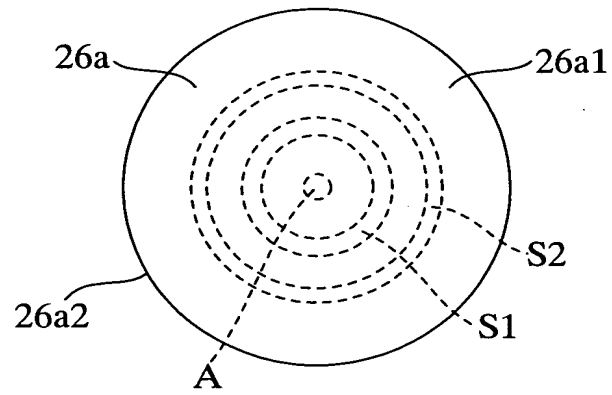
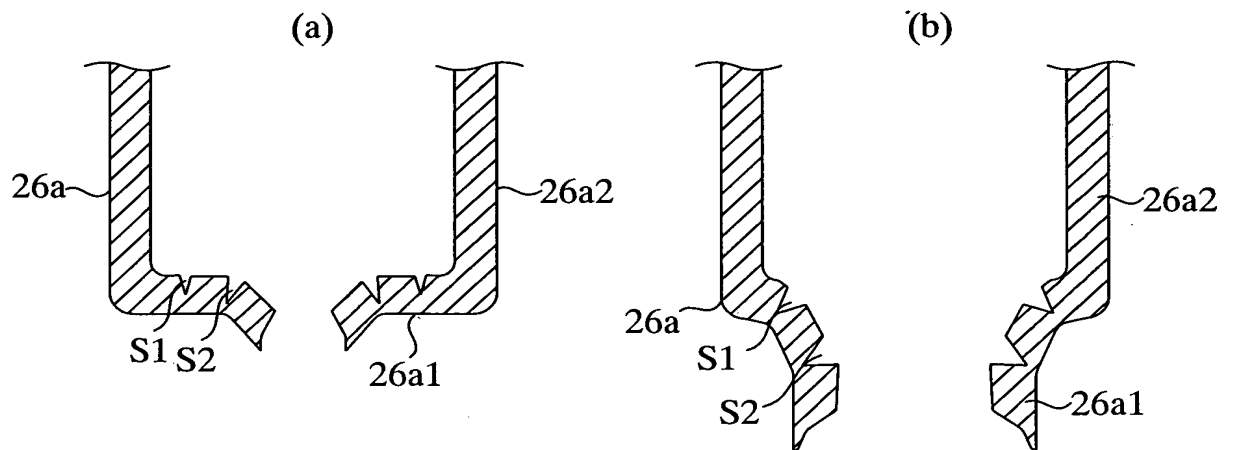


FIG. 8



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FIG.9

